Title (en)

Patterning process using EB or EUV lithography

Title (de)

Strukturierungsverfahren mittels EB- oder EUV-Lithographie

Title (fr)

Procédé de formation de motifs utilisant la lithographie par faisceau d'électrons ou par EUV

Publication

EP 2360527 A1 20110824 (EN)

Application

EP 11001082 A 20110210

Priority

JP 2010031030 A 20100216

Abstract (en)

A chemically amplified positive resist composition for EB or EUV lithography is provided comprising (A) a polymer or a blend of polymers wherein a film of the polymer or polymer blend is insoluble in alkaline developer, but turns soluble under the action of acid, (B) an acid generator, (C) a basic compound, and (D) a solvent. The basic compound (C) is a polymer comprising recurring units bearing a side chain having a secondary or tertiary amine structure as a basic active site and constitutes a part or the entirety of the polymer or polymers as component (A).

IPC 8 full level

G03F 7/039 (2006.01); **C08F 212/02** (2006.01); **C08F 220/30** (2006.01); **C08F 220/34** (2006.01); **G03F 7/004** (2006.01); **H01L 21/027** (2006.01)

CPC (source: EP KR US)

G03F 7/004 (2013.01 - KR); **G03F 7/0045** (2013.01 - KR); **G03F 7/0392** (2013.01 - EP KR US); **G03F 7/0395** (2013.01 - EP KR US); **G03F 7/0397** (2013.01 - EP KR US); **H01L 21/027** (2013.01 - KR); **H01L 21/0271** (2013.01 - KR); Y02P 20/55 (2015.11 - EP)

Citation (applicant)

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- JP 2008133312 A 20080612 - MITSUBISHI RAYON CO
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Designated contracting state (EPC)

AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)

BA ME

DOCDB simple family (publication)

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DOCDB simple family (application)

EP 11001082 A 20110210; CN 201110121500 A 20110216; CN 201410505727 A 20110216; JP 2011016371 A 20110128; KR 20110013205 A 20110215; KR 20160152710 A 20161116; TW 100104906 A 20110215; US 201113027356 A 20110215